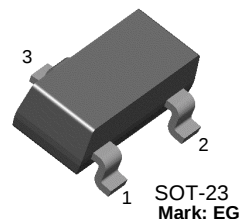


BCW66G

BCW66G

NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 500mA.
- Sourced from process 13.



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings * $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V_{CBO}	Collector-Base Voltage	75	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current - Continuous	1	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	- 55 ~ +150	$^{\circ}\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- These ratings are based on a maximum junction temperature of 150degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}$	75			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$	45			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}$	5			V
I_{CES}	Collector Cut-off Current	$V_{CB} = 45\text{V}, I_E = 0$ $V_{CB} = 45\text{V}, I_E = 0$ $T_A = 150^{\circ}\text{C}$			20 20	nA μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 4\text{V}$			20	nA
h_{FE}	DC Current Gain	$V_{CE} = 10\text{V}, I_C = 100\mu\text{A}$ $V_{CE} = 1\text{V}, I_C = 10\text{mA}$ $V_{CE} = 1\text{V}, I_C = 100\text{mA}$ $V_{CE} = 2\text{V}, I_C = 500\text{mA}$	50 110 160 60		400	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100\text{mA}, I_B = 10\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$			0.3 0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 500\text{mA}, I_B = 50\text{mA}$			2	V
C_{obo}	Output Capacitance	$V_{CB} = 10\text{V}, f = 1\text{MHz}$			12	pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5\text{V}, f = 1\text{MHz}$			80	pF
f_T	Current gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 20\text{mA},$ $f = 100\text{MHz}$	100			MHz
NF	Noise Figure	$V_{CE} = 5\text{V}, I_C = 0.2\text{mA}, R_S = 1\text{k}\Omega,$ $f = 1\text{KHz}, BW = 200\text{Hz}$			10	dB
t_{on}	Turn-On Time	$I_{B1} = I_{B2} = 15\text{mA}$			100	ns
t_{off}	Turn-Off Time	$I_C = 150\text{mA}, R_L = 150\Omega$			400	

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units
P_D	Total Device Dissipation Derate above 25°C			350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient			357	°C/W

Package Dimensions

SOT-23



Dimensions in Millimeters

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